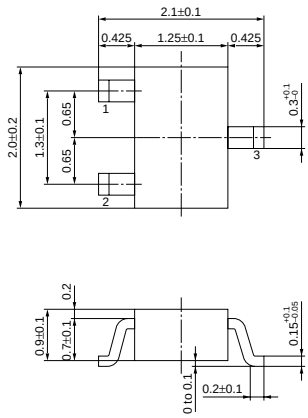
2SC5190

Silicon NPN epitaxial planer type

For low-voltage high-frequency amplification

Unit: mm



1:Base
2:Emitter EIAJ:SC–70
3:Collector S–Mini Type Package

Marking symbol : 3Y

Features

- High transition frequency f_T.
- Small collector output capacitance C_{ob}.
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

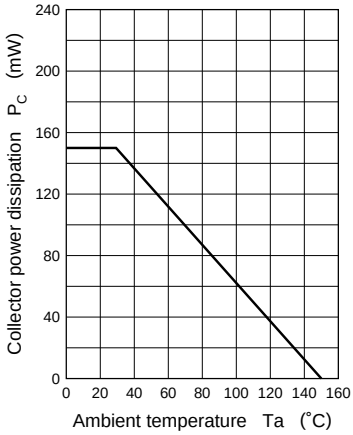
Absolute Maximum Ratings (Ta=25˚C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	9	V
Collector to emitter voltage	V_{CEO}	6	V
Emitter to base voltage	V_{EBO}	2	V
Collector current	I_C	30	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	˚C
Storage temperature	T_{stg}	–55 ~ +150	˚C

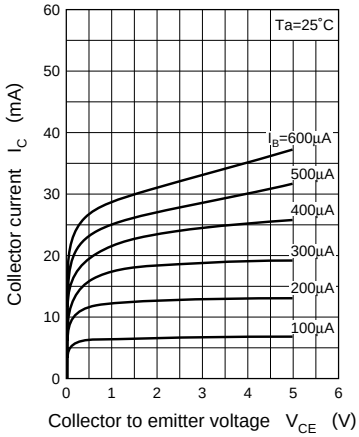
Electrical Characteristics (Ta=25˚C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 5V, I_E = 0			1	μA
Emitter cutoff current	I_{EBO}	V_{EB} = 1V, I_C = 0			1	μA
Forward current transfer ratio	h_{FE}	V_{CE} = 3V, I_C = 10mA	40	100	160	
Collector output capacitance	C_{ob}	V_{CB} = 3V, I_E = 0, f = 1MHz		0.4	0.7	pF
Transition frequency	f_T	V_{CE} = 3V, I_C = 10mA, f = 1.5GHz		10		GHz
Foward transfer gain	$\|S_{21e}\|^2$	V_{CE} = 0.3V, I_C = 1mA, f = 0.9GHz		6.5		dB
Noise figure	NF	V_{CE} = 0.3V, I_C = 1mA, f = 0.9GHz		1.7		dB

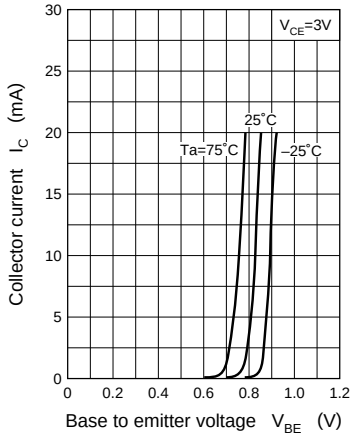
P_C — Ta



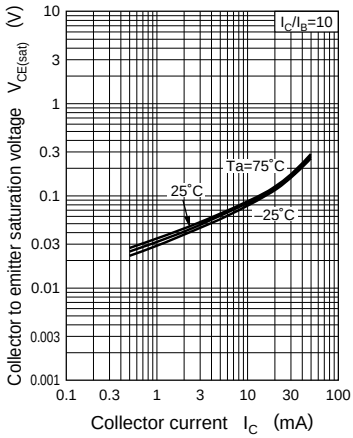
I_C — V_{CE}



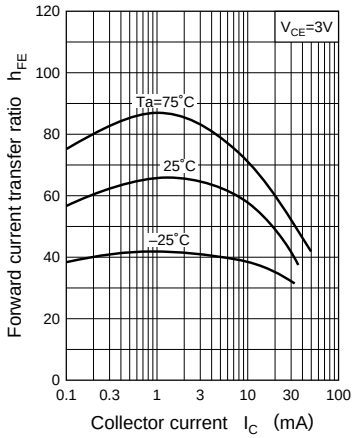
I_C — V_{BE}



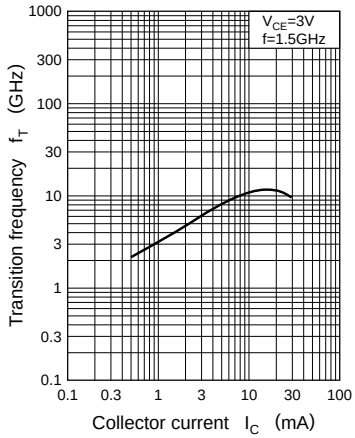
$V_{CE(sat)}$ — I_C



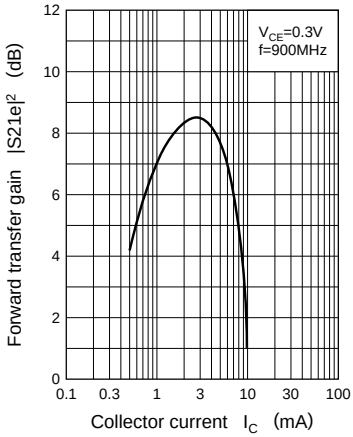
h_{FE} — I_C



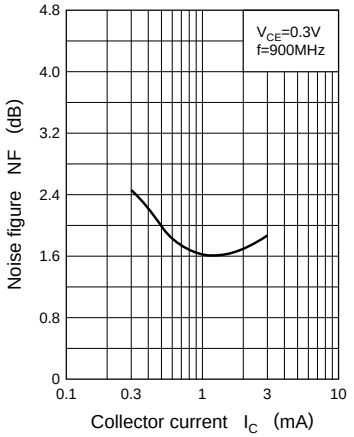
f_T — I_C



$|S_{21e}|^2$ — I_C



NF — I_C



C_{ob} — V_{CB}